

MSKSEMI

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT

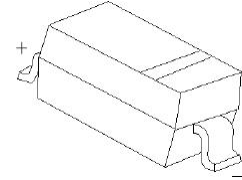


PLED

Product data sheet

FEATURES

For use in low voltage, high frequency inverters
 Free wheeling, and polarity protection applications.

SOD-123


MARKING: B5817W-MS: SJ
 B5818W-MS:SK
 B5819W-MS: SL

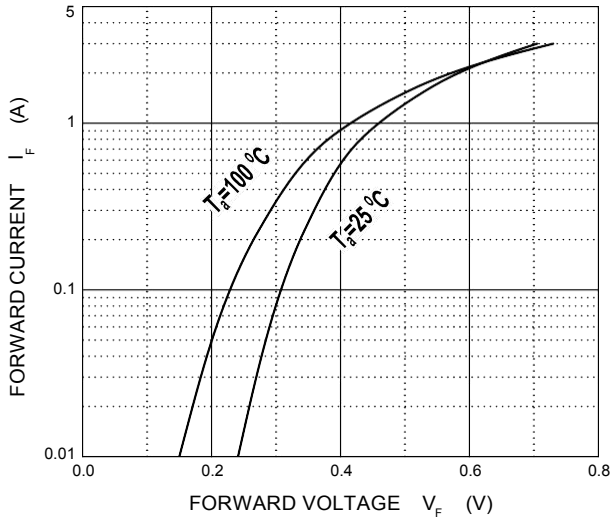

Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25°C

Parameter	Symbol	B5817W-MS	B5818W-MS	B5819W-MS	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	20	30	40	V
Peak Repetitive Peak Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	20	30	40	V
RMS Reverse Voltage	$V_{R(RMS)}$	14	21	28	V
Average Rectified Output Current	I_O	1			A
Peak Forward Surge Current @t=8.3ms	I_{FSM}	9			A
Repetitive Peak Forward Current	I_{FRM}	1.5			A
Power Dissipation	P_D	500			mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	200			°C/W
Junction temperature	T_J	125			°C
Storage Temperature	T_{STG}	-55~+150			°C

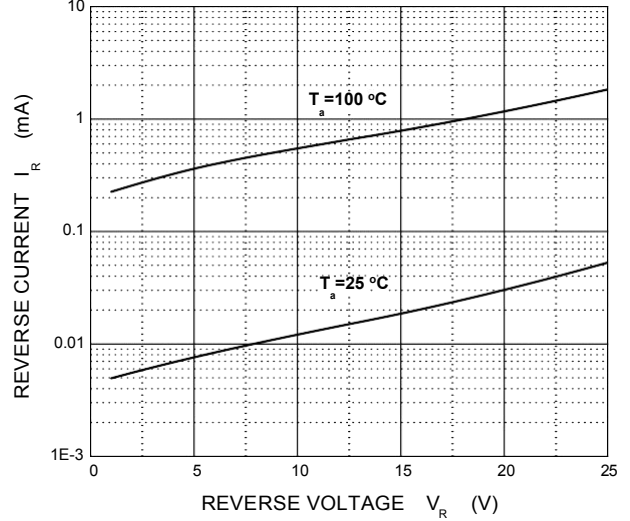
ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 1mA$ B5817W-MS B5818W-MS B5819W-MS	20 30 40		V
Reverse voltage leakage current	I_R	$V_R = 20V$ B5817W-MS $V_R = 30V$ B5818W-MS $V_R = 40V$ B5819W-MS		1	mA
Forward voltage	V_F	B5817W-MS $I_F = 1A$		0.45	v
		B5817W-MS $I_F = 3A$		0.75	v
		B5818W-MS $I_F = 1A$ B5818W-MS $I_F = 3A$		0.55 0.875	v
	V_F	B5819W-MS $I_F = 1A$ B5819W-MS $I_F = 3A$		0.6 0.9	v
Diode capacitance	C_D	$V_R = 4V, f = 1MHz$		120	pF

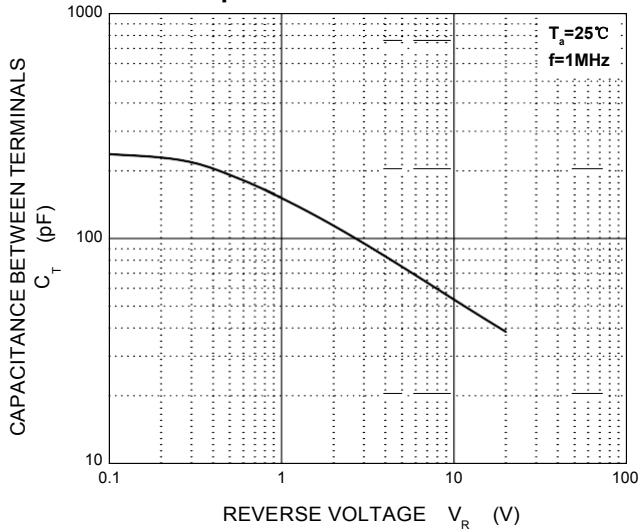
Forward Characteristics



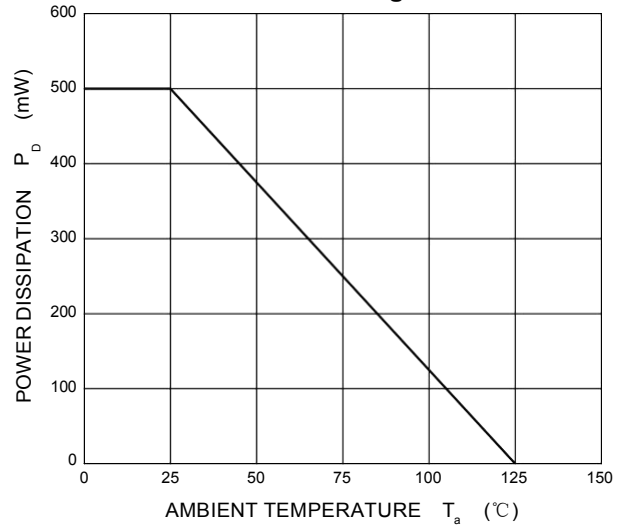
Reverse Characteristics



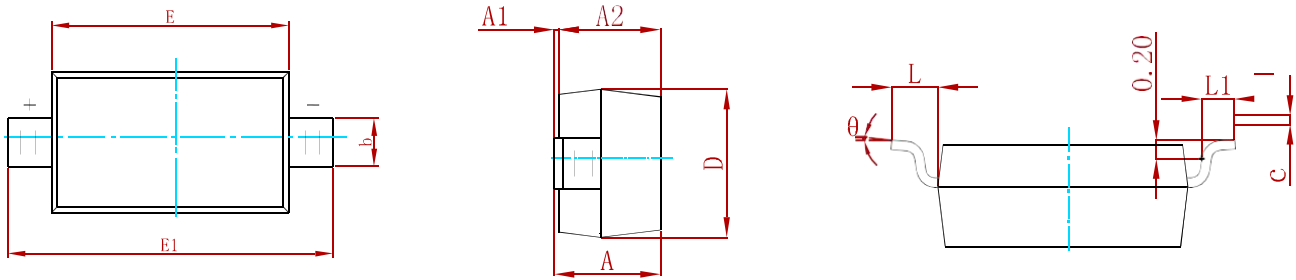
Capacitance Characteristics



Power Derating Curve

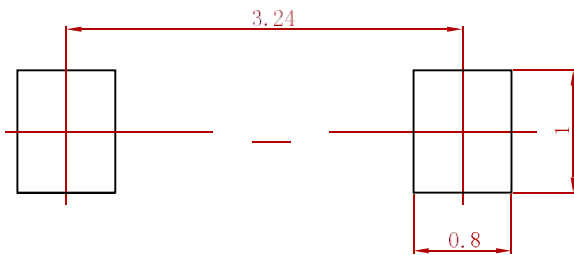


PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.450	0.650	0.018	0.026
c	0.080	0.150	0.003	0.006
D	1.500	1.700	0.059	0.067
E	2.600	2.800	0.102	0.110
E1	3.550	3.850	0.140	0.152
L	0.500 REF		0.020 REF	
L1	0.250	0.450	0.010	0.018
θ	0°	8°	0°	8°

Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.05mm.
3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
B5817W-MS	SOD-123	3000
B5818W-MS	SOD-123	3000
B5819W-MS	SOD-123	3000

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